

YJ Planar Schottky Barrier Diode Die Specification

200V 20A, 102mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB102H200AS-280A

Main Products Characterstics

Maximum Ratings			Static Electrical Characteristics (Ta = 25°C)			
					Value	
					Spec	Typical
					210 V	230V
current (tp = 8.3 ms, halfwave, 1 cycle)	IFSM	150 A	Maximum forward voltage drop			
			IF = 20 A	VF	0.92V	0.88V
			≤ 2%			
Maximum operating junction					3uA	0.3uA

Device Schematics and Outline Drawing

Die Thickness *	11 Mils
Die Size **	
Top Metal Pad	2*48.6*98 Mils
Active Area	2*43.8*93.4 Mils
Space between die	0.98 Mils
Top Metal	AL
Back Metal	Ag
Note: 1 * : Also can offer device with 8 mils thickness	
2 **: Cutting street width is around 1.5 mils	

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:
does not guarantee device performance after assembly.	Store in original container, in dessicated nitrogen, with no contamination.
All operating parameters must be validated for each customer application by customer's technical experts.	Shelf life for parts stored in above condition is 2 years.
Data sheet information is subjected to change without notice.	If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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